

General Description

The AGM60P06S combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductiveloss
- Low Gate Charge for fast switching
- Low Thermal resistance

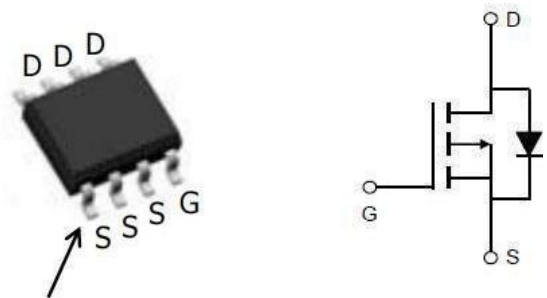
Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
-60V	48mΩ	-5.7A

SOP-8 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM60P06S	AGM60P06S	SOP8	----	----	3000

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	-60	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(TA=25°C) (Note 1)	-5.7	A
	Drain Current-Continuous(TA=100°C)	-2.6	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 2)	-22.8	A
PD	Maximum Power Dissipation(TA=25°C)	2.5	w
	Maximum Power Dissipation(TA=100°C)	1.0	w
EAS	Avalanche energy (Note 3)	18	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	50	°C/W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=-250μA	-60	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=-30V,VGS=0V	--	--	-1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=-250μA	-1.1	-1.7	-2.5	V
gFS	Forward Transconductance	VDS=5V,ID=-12A	--	7.0	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=-10V, ID=-3A	--	53	67	mΩ
		VGS=-4.5V, ID=-2A	--	67	88	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=0V,VGS=0V, F=1MHZ	--	1200	--	pF
Coss	Output Capacitance		--	75	--	pF
Crss	Reverse Transfer Capacitance		--	58	--	pF
Rg	Gate resistance	VGS=0V, VDS=-0V,f=1.0MHz	--	7	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=-10V,VDS=-30V, RL=2.5Ω,RGEN=3Ω	--	10	--	nS
tr	Turn-on Rise Time		--	6.0	--	nS
td(off)	Turn-Off Delay Time		--	40	--	nS
tf	Turn-Off Fall Time		--	13	--	nS
Qg	Total Gate Charge	VGS=-10V, VDS=-30V, ID=-3A	--	25	--	nC
Qgs	Gate-Source Charge		--	5.8	--	nC
Qgd	Gate-Drain Charge		--	3.1	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	-5.7	A
VSD	Forward on Voltage	VGS=0V,IS=-2A	--	-0.8	-1.2	V
trr	Reverse Recovery Time	IF=-25A , dI/dt=100A/μs , TJ=25℃	--	50	--	ns
Qrr	Reverse Recovery Charge		--	105	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25°C

P-Channel Typical Characteristics

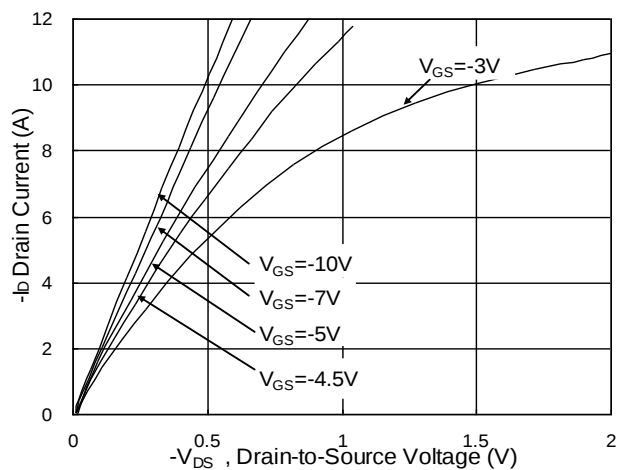


Fig.1 Typical Output Characteristics

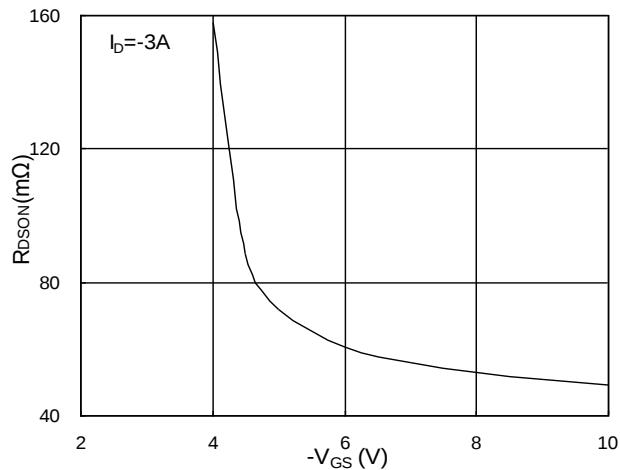


Fig.2 On-Resistance v.s Gate-Source

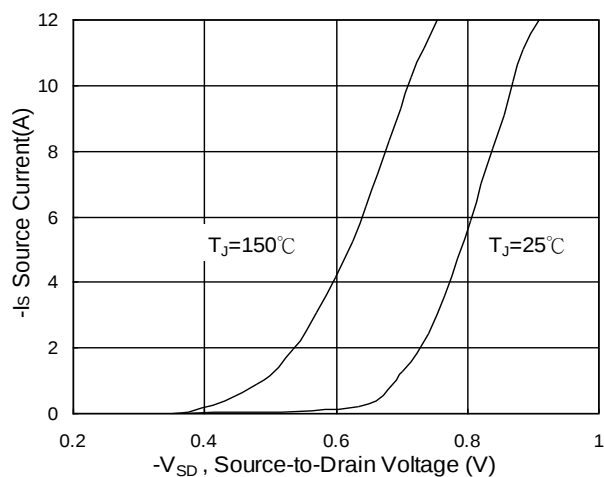


Fig.3 Forward Characteristics of Reverse

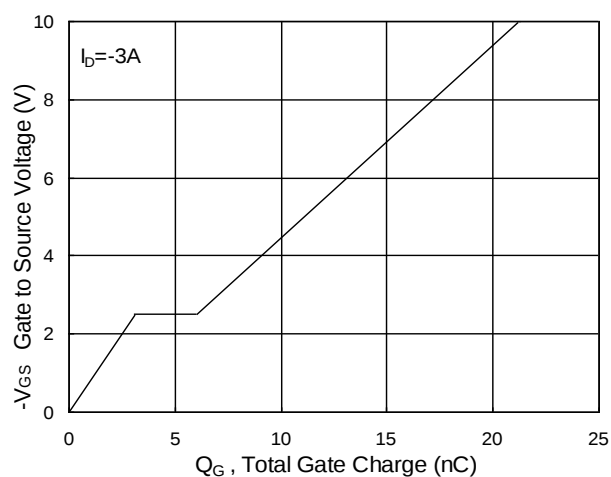


Fig.4 Gate-Charge Characteristics

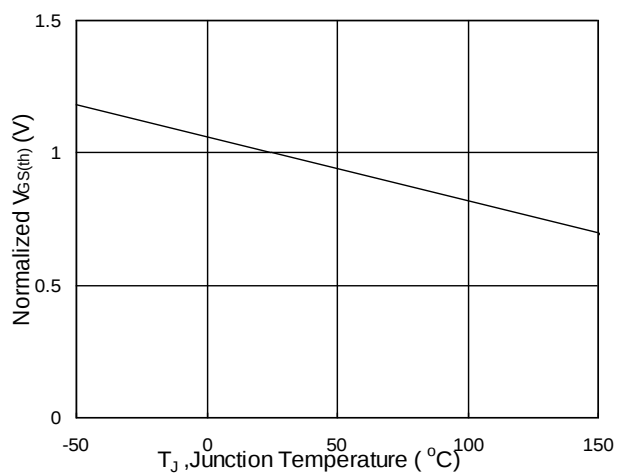


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

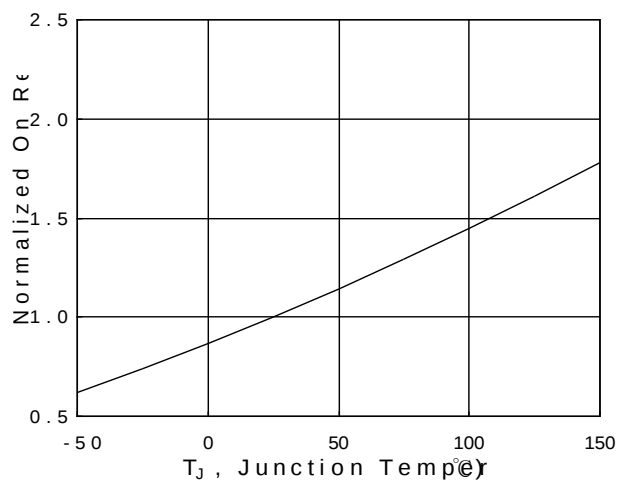
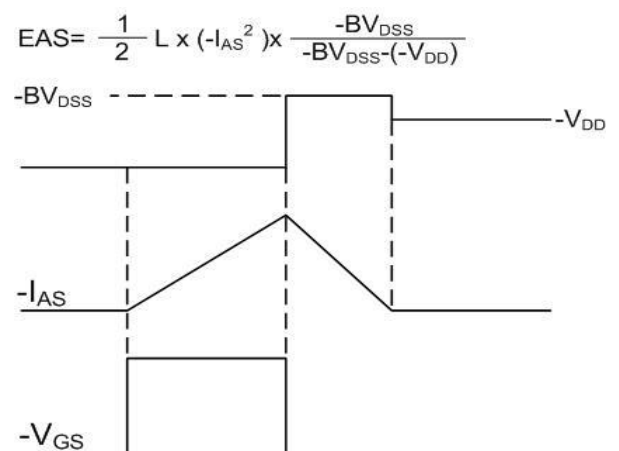
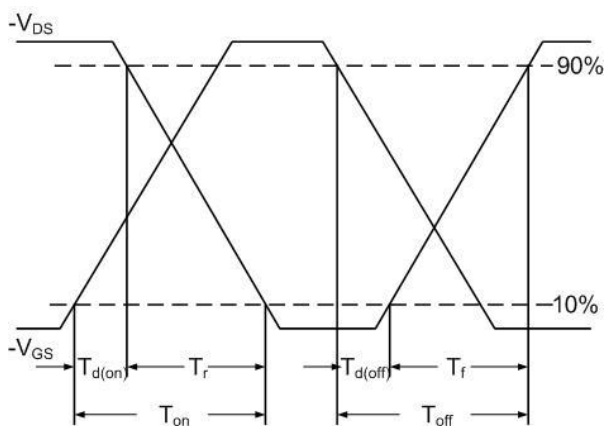
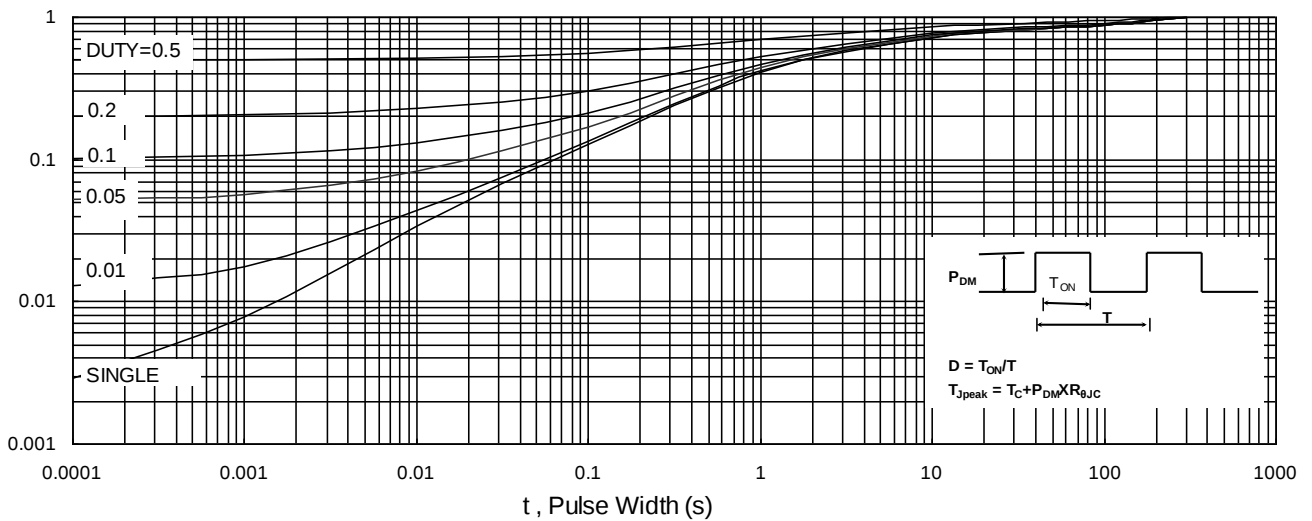
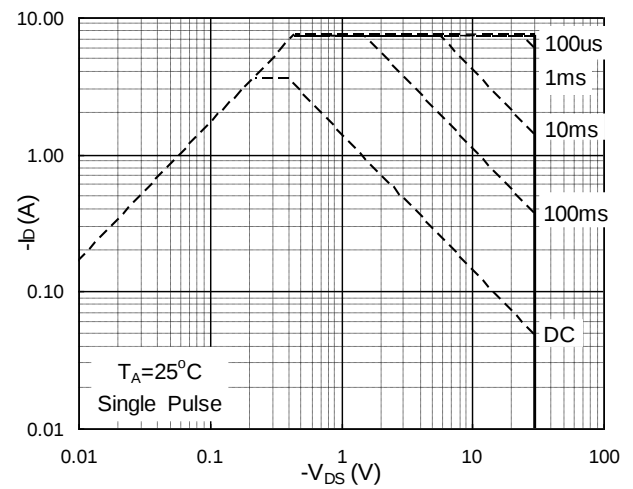
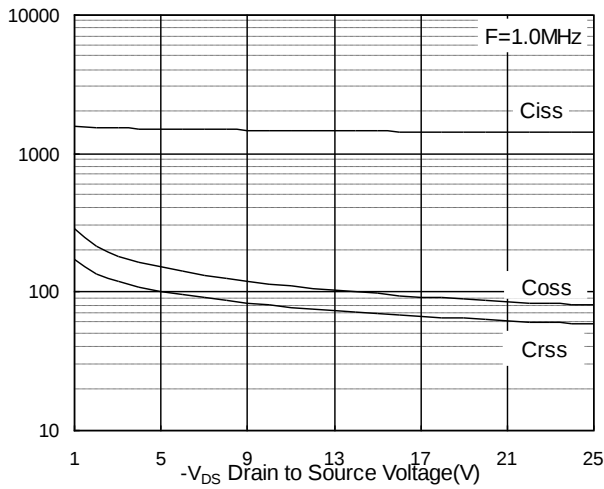


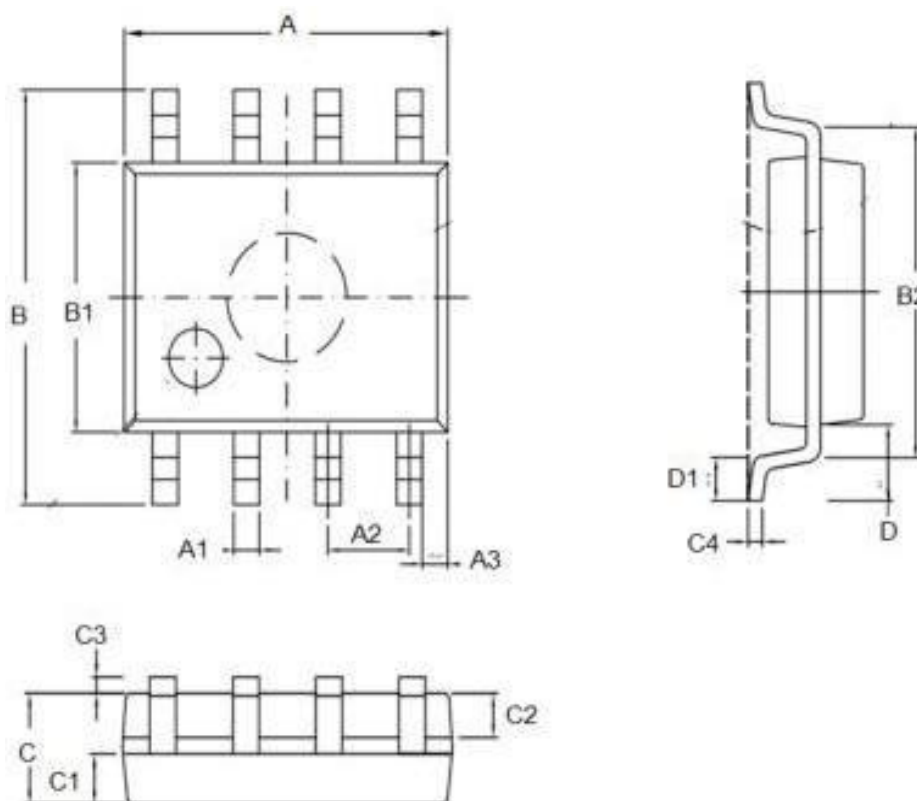
Fig.6 Normalized $R_{DS(on)}$ v.s T_J

P-Channel Typical Characteristics



Dimensions(SOP8)

SYMBOL	min	TYP	max	SYMBOL	min		max
A	4.80		5.00	C	1.30		1.50
A1	0.37		0.47	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.20
B	5.80		6.20	C4	0.19	0.20	0.23
B1	3.80		4.00	D		1.05	
B2		5.00		D1	0.40		0.62



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